

## 2SK1521, 2SK1522

Silicon N Channel MOS FET

REJ03G0949-0200  
(Previous: ADE-208-1289)  
Rev.2.00  
Sep 07, 2005

### Application

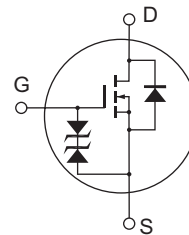
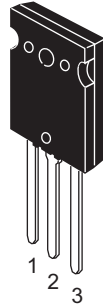
High speed power switching

### Features

- Low on-resistance
- High speed switching
- Low drive current
- Built-in fast recovery diode ( $t_{tr} = 120$  ns)
- Suitable for motor control, switching regulator, DC-DC converter

### Outline

RENESAS Package code: PRSS0004ZF-A  
(Package name: TO-3PL)



1. Gate
2. Drain
3. Source

## Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	2SK1521	450	V
	2SK1522	500	
Gate to source voltage	V <sub>GSS</sub>	±30	V
Drain current	I <sub>D</sub>	50	A
Drain peak current	I <sub>D(pulse)</sub> *1	200	A
Body to drain diode reverse drain current	I <sub>DR</sub>	50	A
Channel dissipation	P <sub>ch</sub> *2	250	W
Channel temperature	T <sub>ch</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

Notes: 1. PW ≤ 10 μs, duty cycle ≤ 1%

2. Value at T<sub>C</sub> = 25°C

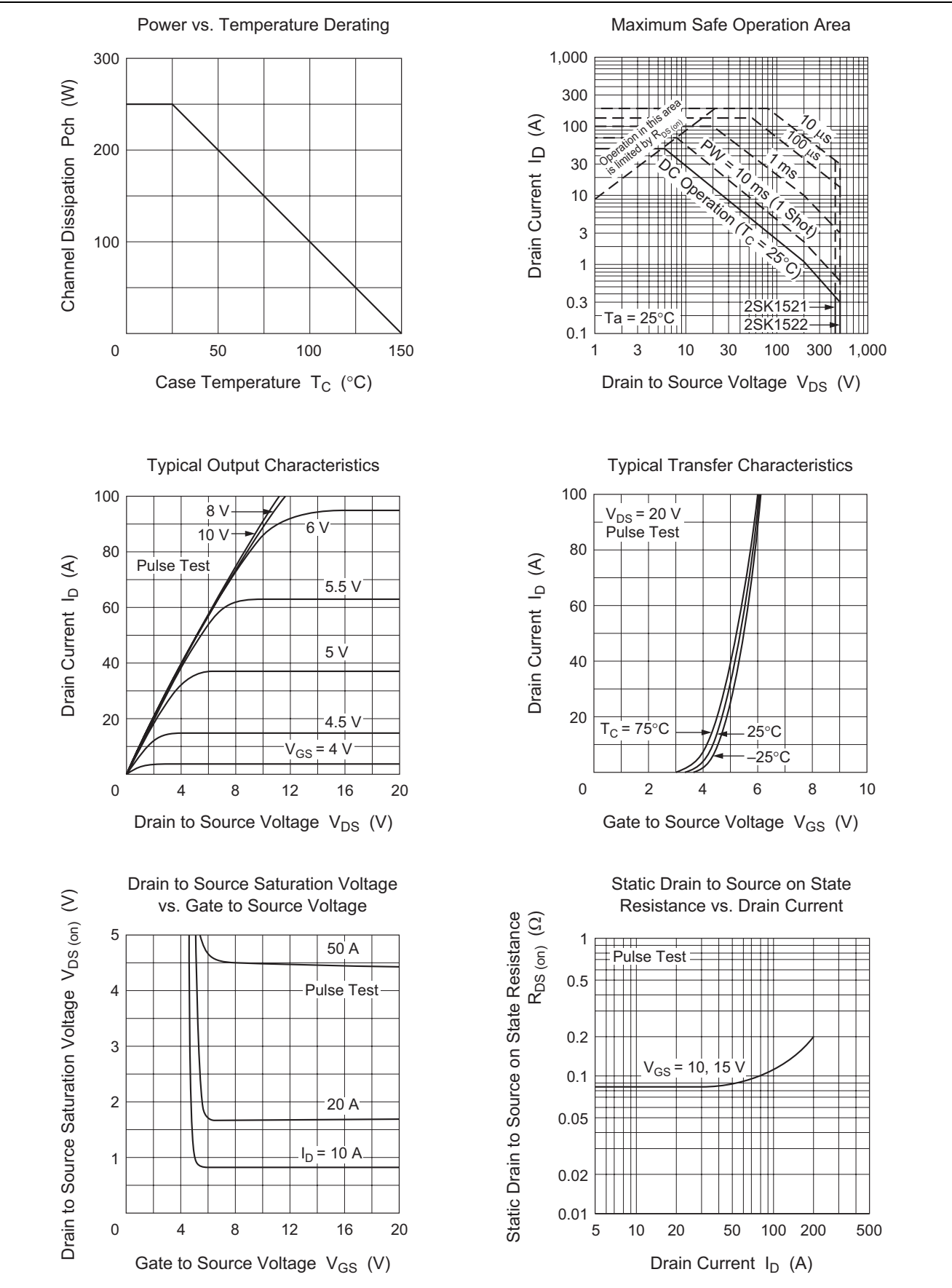
## Electrical Characteristics

(Ta = 25°C)

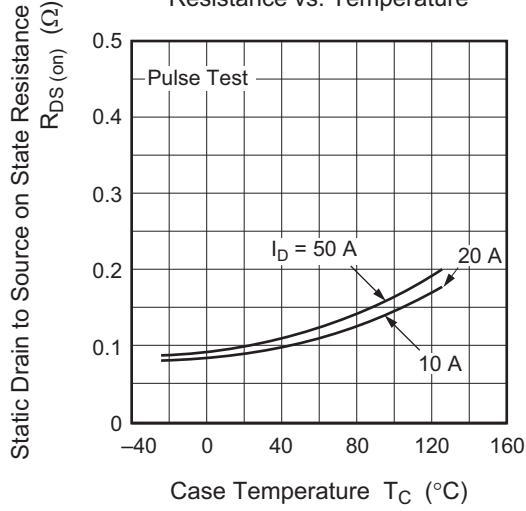
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	2SK1521	450	—	—	V	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0
	2SK1522	500				
Gate to source breakdown voltage	V <sub>(BR)GSS</sub>	±30	—	—	V	I <sub>G</sub> = ±100 μA, V <sub>DS</sub> = 0
Gate to source leak current	I <sub>GSS</sub>	—	—	±10	μA	V <sub>GS</sub> = ±25 V, V <sub>DS</sub> = 0
Zero gate voltage drain current	2SK1521	—	—	250	μA	V <sub>DS</sub> = 360 V, V <sub>GS</sub> = 0
	2SK1522					V <sub>DS</sub> = 400 V, V <sub>GS</sub> = 0
Gate to source cutoff voltage	V <sub>GS(off)</sub>	2.0	—	3.0	V	I <sub>D</sub> = 1 mA, V <sub>DS</sub> = 10 V
Static drain to source on state resistance	2SK1521	—	0.08	0.10	Ω	I <sub>D</sub> = 25 A, V <sub>GS</sub> = 10 V *3
	2SK1522	—	0.085	0.11		
Forward transfer admittance	y <sub>fs</sub>	22	35	—	S	I <sub>D</sub> = 25 A, V <sub>DS</sub> = 10 V *3
Input capacitance	C <sub>iss</sub>	—	8700	—	pF	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0, f = 1 MHz
Output capacitance	C <sub>oss</sub>	—	2400	—	pF	
Reverse transfer capacitance	C <sub>rss</sub>	—	235	—	pF	
Turn-on delay time	t <sub>d(on)</sub>	—	85	—	ns	
Rise time	t <sub>r</sub>	—	250	—	ns	I <sub>D</sub> = 25 A, V <sub>GS</sub> = 10 V, R <sub>L</sub> = 1.2 Ω
Turn-off delay time	t <sub>d(off)</sub>	—	600	—	ns	
Fall time	t <sub>f</sub>	—	250	—	ns	
Body to drain diode forward voltage	V <sub>DF</sub>	—	1.1	—	V	I <sub>F</sub> = 50 A, V <sub>GS</sub> = 0
Body to drain diode reverse recovery time	t <sub>rr</sub>	—	120	—	ns	I <sub>F</sub> = 50 A, V <sub>GS</sub> = 0, di <sub>F</sub> /dt = 100 A/μs

Note: 3. Pulse test

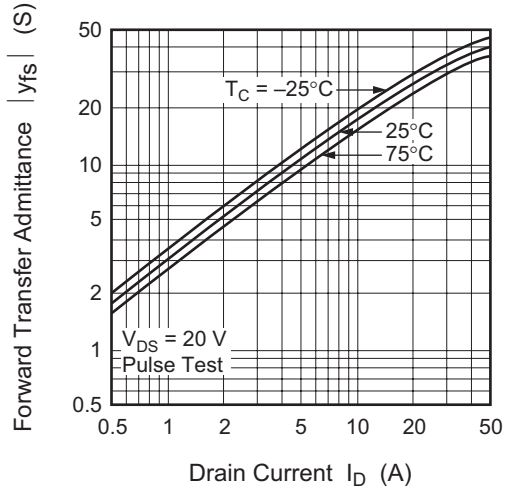
查看"2SK1521"供应商



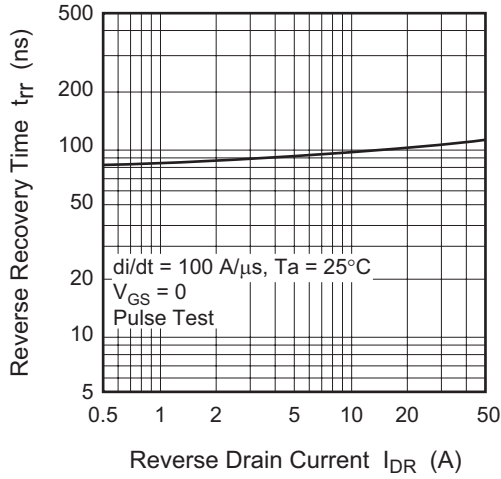
查询"2SK1521-5"供应商 **Static Drain to Source on State Resistance vs. Temperature**



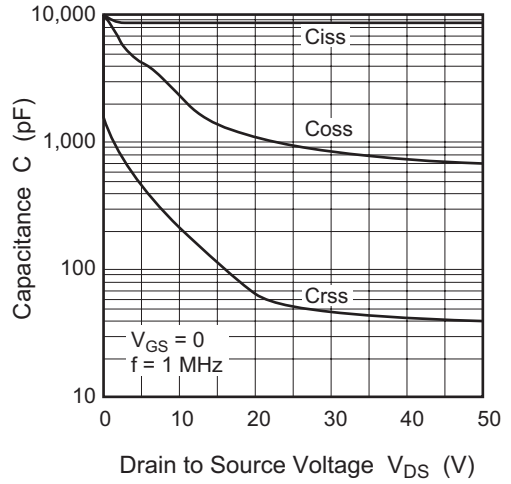
**Forward Transfer Admittance vs. Drain Current**



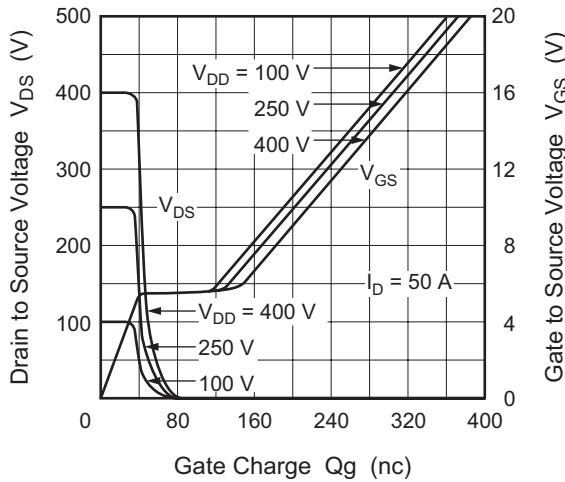
**Body to Drain Diode Reverse Recovery Time**



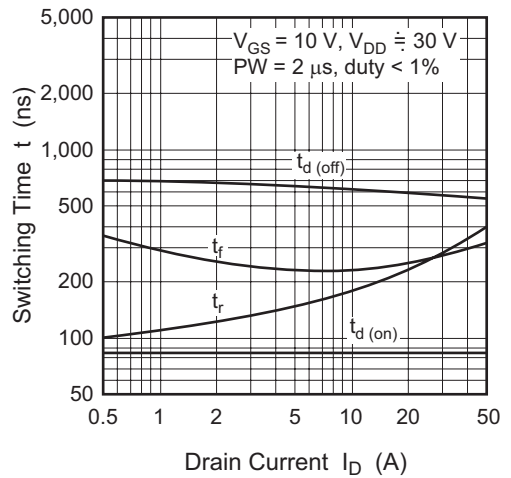
**Typical Capacitance vs. Drain to Source Voltage**



**Dynamic Input Characteristics**

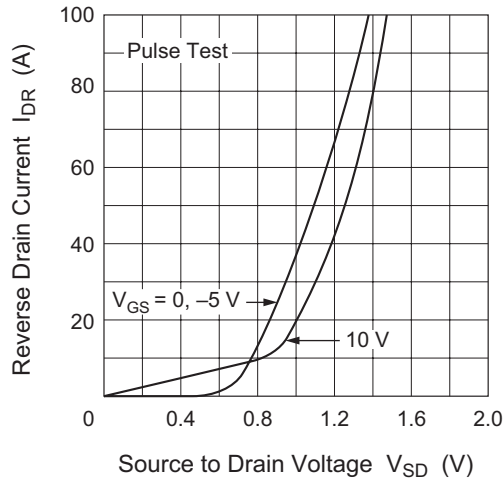


**Switching Characteristics**

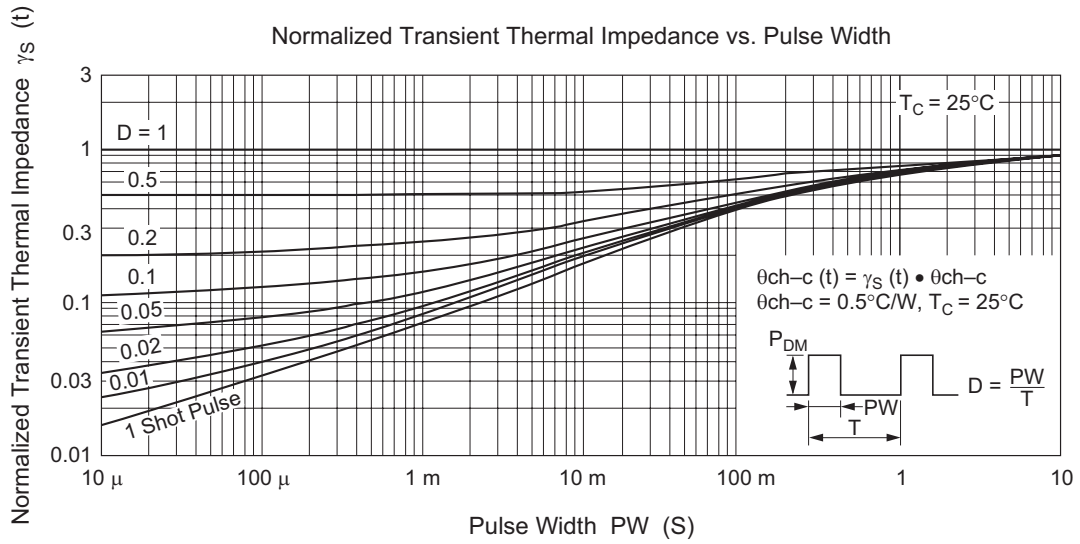


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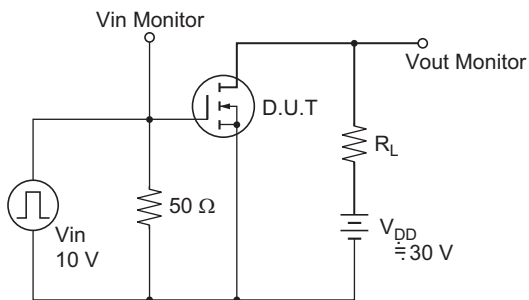
Reverse Drain Current vs. Source to Drain Voltage



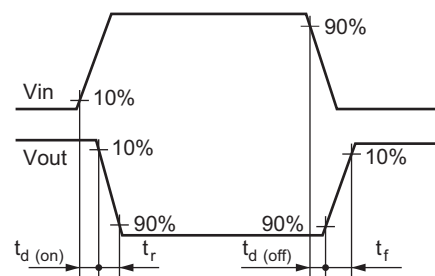
Normalized Transient Thermal Impedance vs. Pulse Width



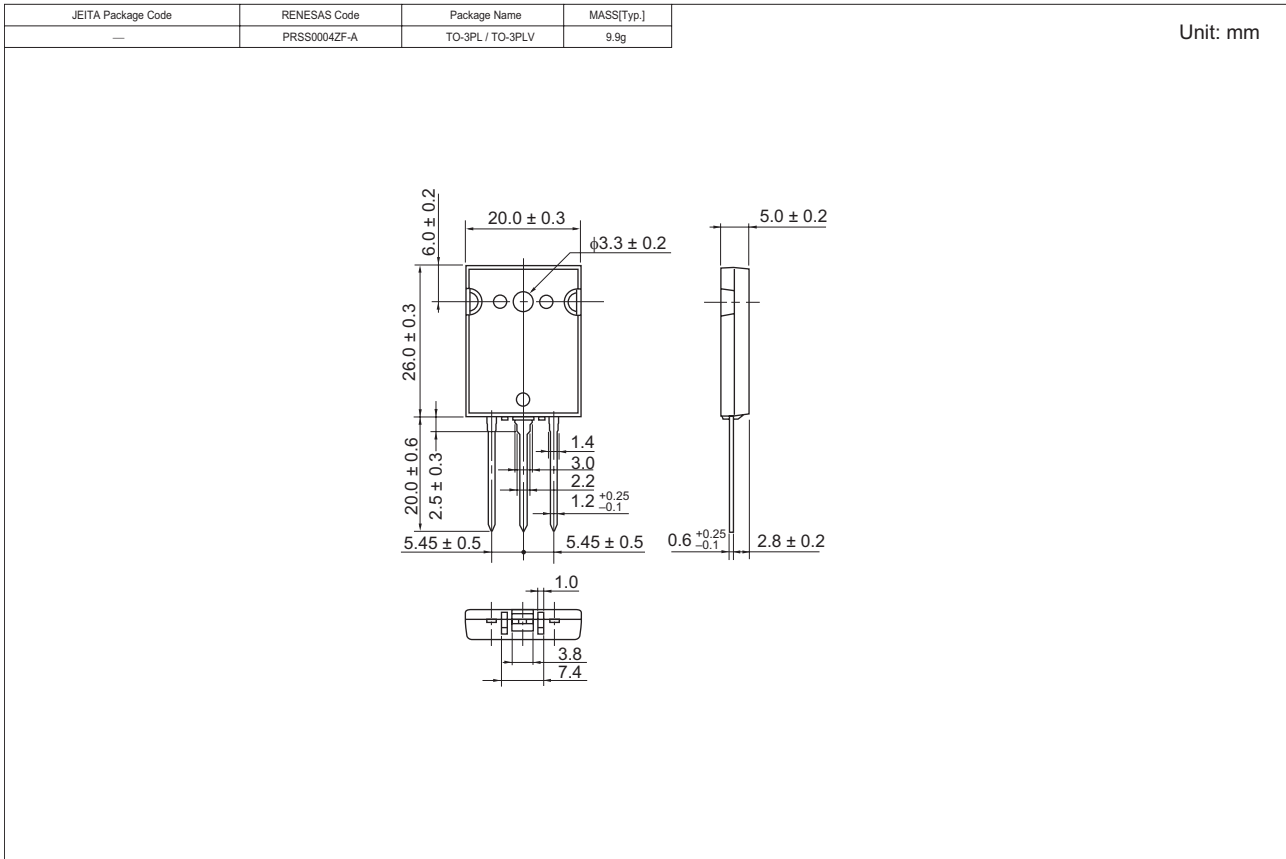
Switching Time Test Circuit



Waveforms



Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
2SK1521-E	500 pcs	Box (Case)
2SK1522-E	500 pcs	Box (Case)

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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